

G D S Top View Vishay Siliconix

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.006				
I <sub>D</sub> (A)	120				
Configuration	Single				

# TO-263 G G

#### N-Channel MOSFET

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- 100 % Rq and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM120N06-06-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	60	- V	
Gate-Source Voltage		$V_{GS}$	± 20		
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	I <sub>D</sub>	120		
	T <sub>C</sub> = 125 °C		80		
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	120	Α		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	480			
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	65		
Single Pulse Avalanche Energy	L=0.11IIII	E <sub>AS</sub>	211	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	230	W	
Maximum Fower Dissipation	T <sub>C</sub> = 125 °C		76	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient PC	CB Mount <sup>c</sup>	$R_{thJA}$	40	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	0.65		

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							L	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		60	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		2.5	3.0	3.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1.0		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	1	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	250	250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A	-	0.0045	0.0060		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C	-	-	0.0104	Ω	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C	-	-	0.0129		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		94	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	5196	6495		
Output Capacitance	Coss	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	708	885	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			ı	336	420		
Total Gate Charge <sup>c</sup>	Qg			1	96.5	145		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_D = 75 \text{ A}$	-	24.6	-	nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			1	27.2	ı		
Gate Resistance	$R_{g}$		f = 1 MHz		1.2	1.7	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>				16	24		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 30 \text{ V}, \text{ R}_{L} = 0.4 \Omega$ $I_{D} \cong 75 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	14	21	ns .	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			ı	34	51		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	9	14		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>		_					
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	480	Α	
Forward Voltage	$V_{SD}$	l <sub>F</sub> :	-	0.9	1.5	V		

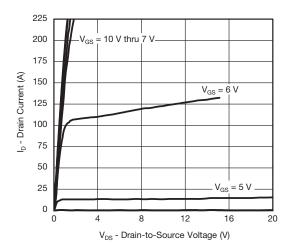
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

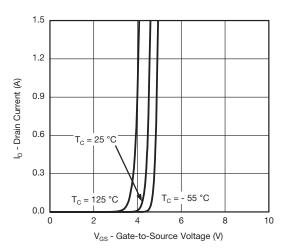
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



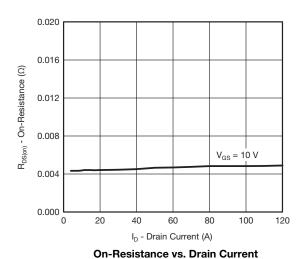
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

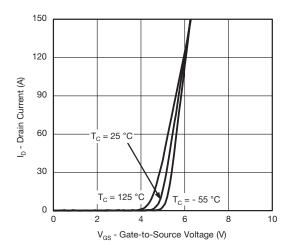


#### **Output Characteristics**

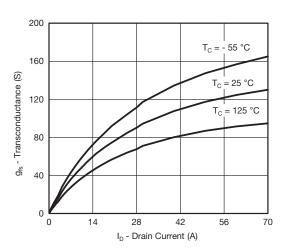


#### **Transfer Characteristics**

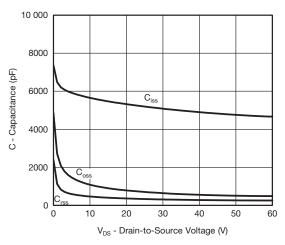




#### **Transfer Characteristics**



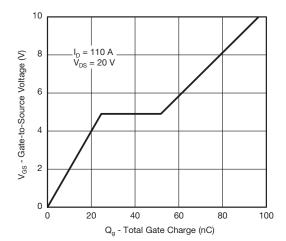
#### Transconductance



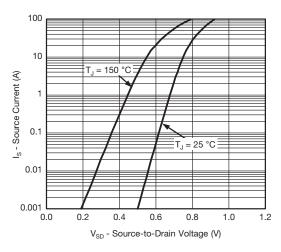
Capacitance



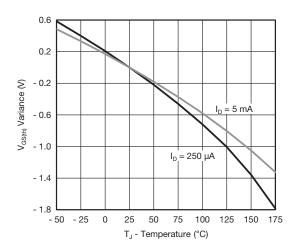
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



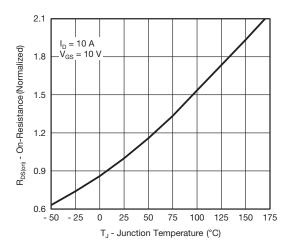
#### **Gate Charge**



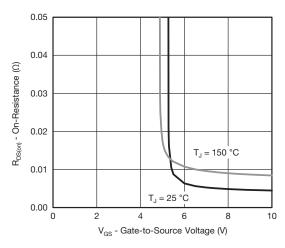
#### Source Drain Diode Forward Voltage



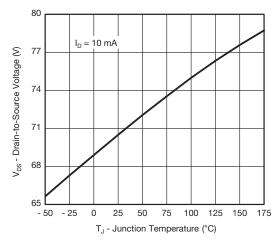
**Threshold Voltage** 



On-Resistance vs. Junction Temperature



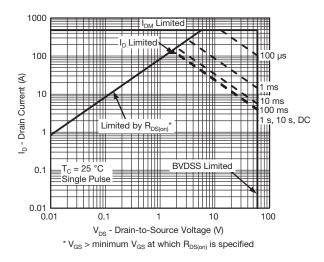
On-Resistance vs. Gate-to-Source Voltage



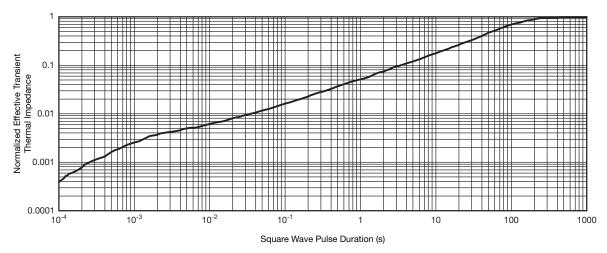
**Drain Source Breakdown vs. Junction Temperature** 



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



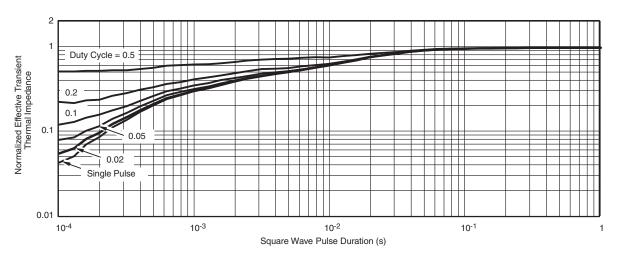
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

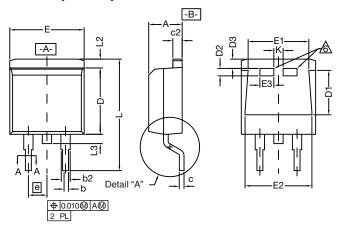
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

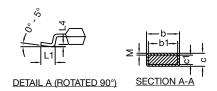
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### TO-263 (D2PAK): 3-LEAD





		INC	HES	MILLIN	METERS	
DIM.		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
b		0.020	0.039	0.508	0.990	
b1		0.020	0.035	0.508	0.889	
b2		0.045	0.055	1.143	1.397	
-*	Thin lead	0.013	0.018	0.330	0.457	
C*	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
D		0.340	0.380	8.636	9.652	
D1		0.220	0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	=	6.223	=	
E2		0.355	0.375	9.017	9.525	
E3		E3 0.072		1.829	1.981	
	е	0.100 BSC		2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
М		-	0.002	-	0.050	
ECN: T10-0738-Rev. J, 03-Jan-11 DWG: 5843						

DWG: 5843

#### Notes

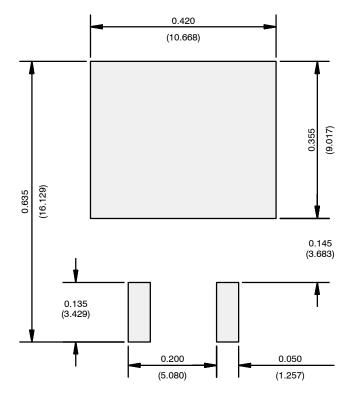
- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.
- his feature is for thick lead.

Document Number: 71198 Revison: 03-Jan-11





## RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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